PCN Number:	20240313001.1	PCN Date:	March 14, 2024
Title:	Qualification of RFAB using qualified Process Technology, Die Revision and additional Assembly BOM options for select devices		
Customer Contact:	Change Management team	Dept:	Quality Services
Proposed 1st Ship Date:	June 12, 2024	Sample requests accepted until:	April 13, 2024*

*Sample requests received after April 13, 2024 will not be supported.

Change Type:

☐	Assembly Site	☒	Design	☐	Wafer Bump Material
☒	Assembly Process	☐	Data Sheet	☐	Wafer Bump Process
☒	Assembly Materials	☐	Part number change	☒	Wafer Fab Site
☐	Mechanical Specification	☐	Test Site	☒	Wafer Fab Material
☒	Packing/Shipping/Labeling	☐	Test Process	☐	Wafer Fab Process

PCN Details

Description of Change:

Texas Instruments is pleased to announce the qualification of its RFAB fabrication facility as an additional Wafer Fab option in addition to an Assembly BOM option for the devices listed below.

Current Fab Site			Additional Fab Site		
Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter
MIHO8	LBC8LVISO	200 mm	RFAB	LBC8LVISO	300 mm

The die was also changed as a result of the process change.

Construction differences are as follows:

	Current	Proposed
Bond wire type, diam	0.96mil Au	0.8mil Cu

Qual details are provided in the Qual Data Section.

Reason for Change:

Continuity of Supply

1) To align with world technology trends and use wiring with enhanced mechanical and electrical properties
2) Maximize flexibility within our Assembly/Test production sites.
3) Cu is easier to obtain and stock

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Impact on Environmental Ratings

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
☒ No Change	☒ No Change	☒ No Change	☒ No Change

Changes to product identification resulting from this PCN:

Fab Site Information:

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
MIHO8	MH8	JPN	Ibaraki
RFAB	**RFB**	**USA**	**Richardson**

Die Rev:

Current	New
Die Rev [2P]	**Die Rev [2P]**
A	**A**

Sample product shipping label (not actual product label):

Product Affected:

ISO7710DR	ISO7720DWR	ISO7721BDWR	ISO7721FDWR
ISO7710DWR	ISO7720DWVR	ISO7721DWR	ISO7721FDWVR
ISO7710FDR	ISO7720FDWR	ISO7721DWVR	
ISO7710FDWR	ISO7720FDWVR	ISO7721FBDWR	

Qualification Report

Automotive Qualification Summary
(As per AEC-Q100 Rev. J and JEDEC Guidelines)
Approve Date 01-March-2024

Product Attributes

Attributes	Qual Device: ISO7710QDRQ1	QBS Package Reference: ISO6721BQDRQ1	QBS Process Reference: UCC23513QDWYQ1	QBS Package Reference: ISO6763QDWRQ1	QBS Package Reference: ISO5452DWR	QBS Package Reference: ISO7721QDRQ1	QBS Package Reference: UCC21330BQDRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Interface	Interface	Power Management	Interface	Power Management	Signal Chain,Interface	Power Management
Wafer Fab Supplier	RFAB, RFAB	MH8, MH8	RFAB, RFAB	RFAB, RFAB	DP1DM5, DP1DM5, MH8	RFAB, RFAB	RFAB, RFAB, RFAB
Assembly Site	MLA	MLA	TAI	MLA	MLA	MLA	MLA
Package Group	SOIC	SOIC	SOIC	SOIC	SOIC	SOIC	SOIC
Package Designator	D	D	DWY	DW	DW	D	D
Pin Count	8	8	6	16	16	8	16

QBS: Qual By Similarity
Qual Device ISO7710QDRQ1 is qualified at MSL2 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO7710QDRQ1	QBS Package Reference: ISO6721BQDRQ1	QBS Process Reference: UCC23513QDWYQ1	QBS Package Reference: ISO6763QDWRQ1	QBS Package Reference: ISO5452DWR	QBS Package Reference: ISO7721QDRQ1	QBS Package Reference: UCC21330BQDRQ1
Test Group A - Accelerated Environment Stress Tests														
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	-	-	No Fails	-	-	-	-	-
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL2 260C	-	-	-	-	No Fails	No Fails	No Fails	No Fails
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	3/231/0	-	3/231/0	1/77/0	-	-
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Autoclave	121C/15psig	96 Hours	-	3/231/0	-	3/231/0	1/77/0	-	-
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	-	3/231/0	-	3/231/0	1/77/0	1/77/0	3/231/0
TC-SAM	A4	-	3	3	Post TC SAM	<50% delamination	-	-	1/12/0	-	1/12/0	-	1/12/0	1/12/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	-	-	-	3/135/0	1/45/0	-	-
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	175C	500 Hours	-	3/135/0	-	-	-	-	-
Test Group B - Accelerated Lifetime Simulation Tests														
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	125C	1000 Hours	-	3/231/0	3/231/0	-	-	-	-
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate	125C	48 Hours	-	-	3/2400/0	-	-	-	-
Test Group C - Package Assembly Integrity Tests														
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	-	3/228/0	-	3/90/0	-	1/30/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	-	3/228/0	-	3/90/0	-	1/30/0	3/90/0
SD	C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	1/15/0	-	-	-	-	-
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	1/15/0	-	-	-	-	-
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions	Cpk>1.67	-	-	3/30/0	-	-	-	1/10/0	3/30/0
Test Group D - Die Fabrication Reliability Tests														
Type	**#**	**Test Spec**	**Min Lot Qty**	**SS / Lot**	**Test Name**	**Condition**	**Duration**	**Qual Device: ISO7710QDRQ1**	**QBS Package Reference: ISO6721BQDRQ1**	**QBS Process Reference: UCC23513QDWYQ1**	**QBS Package Reference: ISO6763QDWRQ1**	**QBS Package Reference: ISO5452DWR**	**QBS Package Reference: ISO7721QDRQ1**	**QBS Package Reference: UCC21330BQDRQ1**
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
BTI	D4	-	-	-	Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E - Electrical Verification Tests														
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2000 Volts	1/3/0	1/3/0	1/3/0	-	-	1/3/0	1/3/0
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	500 Volts	1/3/0	1/3/0	1/3/0	-	-	1/3/0	1/3/0
LU	E4	AEC Q100-004	1	6	Latch-Up	Per AEC Q100-004	-	1/6/0	1/6/0	1/6/0	-	-	1/6/0	1/6/0
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	1/30/0	3/90/0	3/90/0	3/90/0	1/30/0	1/30/0	1/30/0

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40C to +150C
Grade 1 (or Q): -40C to +125C
Grade 2 (or T): -40C to +105C
Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold : HTOL, ED
Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
Room : AC/uHAST
Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Qualification Report

Automotive Qualification Summary
(As per AEC-Q100 Rev. J and JEDEC Guidelines)
Approve Date 01-MARCH -2024

Product Attributes

Attributes	Qual Device: ISO7710QDWRQ1	QBS Process Reference: UCC23513QDWYQ1	QBS Package Reference: ISO6763QDWRQ1	QBS Package Reference: ISO7721QDWRQ1	QBS Product Reference: ISO7710QDRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Interface	Power Management	Interface	Interface	Interface
Wafer Fab Supplier	RFAB, RFAB	RFAB, RFAB	RFAB, RFAB	RFAB, RFAB	RFAB, RFAB
Assembly Site	MLA	TAI	MLA	MLA	MLA
Package Group	SOIC	SOIC	SOIC	SOIC	SOIC
Package Designator	DW	DWY	DW	DW	D
Pin Count	16	6	16	16	8

QBS: Qual By Similarity
Qual Device ISO7710QDWRQ1 is qualified at MSL2 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO7710QDWRQ1	QBS Process Reference: UCC23513QDWYQ1	QBS Package Reference: ISO6763QDWRQ1	QBS Package Reference: ISO7721QDWRQ1	QBS Product Reference: ISO7710QDRQ1
Test Group A - Accelerated Environment Stress Tests												
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL2 260C	-	-	-	No Fails	-	-
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	-	3/231/0	-	-
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Autoclave	121C/15psig	96 Hours	-	-	3/231/0	-	-
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	-	-	3/231/0	-	-
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	-	-	3/135/0	-	-
Test Group B - Accelerated Lifetime Simulation Tests												
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	125C	1000 Hours	-	3/231/0	-	-	-
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate	125C	48 Hours	-	3/2400/0	-	-	-

Test Group C - Package Assembly Integrity Tests												
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	-	-	3/90/0	1/30/0	-
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	-	-	3/90/0	1/30/0	-
SD	C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	-	-	-	-
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	-	-	-	-
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions	Cpk>1.67	-	-	-	-	1/10/0	-
Test Group D - Die Fabrication Reliability Tests												
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
BTI	D4	-	-	-	Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E - Electrical Verification Tests												
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2000 Volts	Device specific data [1]	1/3/0	-	-	1/3/0
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	500 Volts	Device specific data [1]	1/3/0	-	1/3/0	1/3/0
LU	E4	AEC Q100-004	1	6	Latch-Up	Per AEC Q100-004	-	Device specific data [1]	1/6/0	-	-	1/6/0
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	Device specific data [1]	3/90/0	3/90/0	-	1/30/0

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles
Ambient Operating Temperature by Automotive Grade Level:
Grade 0 (or E): -40C to +150C
Grade 1 (or Q): -40C to +125C
Grade 2 (or T): -40C to +105C
Grade 3 (or I) : -40C to +85C
E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):
Room/Hot/Cold : HTOL, ED
Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
Room : AC/Uhast
[1] Qual Device: ISO7710QDWRQ1 and QBS Reference: ISO7710QDRQ1 use the same silicon die.
Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Qualification Report

Automotive Qualification Summary
(As per AEC-Q100 Rev. H and JEDEC Guidelines)
Approve Date 30-January-2024

Product Attributes

Attributes	Qual Device: ISO7721QDWRQ1	Qual Device: ISO7720QDWRQ1	QBS Process Reference: UCC23513QDWYQ1	QBS Package Reference: ISO6763QDWRQ1	QBS Product Reference: ISO7721QDRQ1	QBS Product Reference: ISO7720QDRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Interface	Interface	Power Management	Interface	Signal Chain,Interface	Signal Chain,Interface
Wafer Fab Supplier	RFAB, RFAB	RFAB, RFAB	RFAB, RFAB	RFAB, RFAB	RFAB, RFAB	RFAB, RFAB
Assembly Site	MLA	MLA	TAI	MLA	MLA	MLA
Package Group	SOIC	SOIC	SOIC	SOIC	SOIC	SOIC
Package Designator	DW	DW	DWY	DW	D	D
Pin Count	16	16	6	16	8	8

QBS: Qual By Similarity
Qual Device ISO7721QDWRQ1 is qualified at MSL2 260C
Qual Device ISO7720QDWRQ1 is qualified at MSL2 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO7721QDWRQ1	Qual Device: ISO7720QDWRQ1	QBS Process Reference: UCC23513QDWYQ1	QBS Package Reference: ISO6763QDWRQ1	QBS Product Reference: ISO7721QDRQ1	QBS Product Reference: ISO7720QDRQ1
Test Group A - Accelerated Environment Stress Tests													
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL2 260C	-	-	-	-	No Fails	No Fails	-
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	-	-	3/231/0	-	-
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Autoclave	121C/15psig	96 Hours	-	-	-	3/231/0	-	-
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	-	-	-	3/231/0	1/77/0	-
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	-	-	-	3/135/0	-	-
Test Group B - Accelerated Lifetime Simulation Tests													
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	125C	1000 Hours	-	-	3/231/0	-	-	-
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate	125C	48 Hours	-	-	3/2400/0	-	-	-
Test Group C - Package Assembly Integrity Tests													
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	-	3/90/0	3/90/0	1/30/0	-
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	-	3/90/0	3/90/0	1/30/0	-
SD	C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	-	1/15/0	-	-	-
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	-	1/15/0	-	-	-
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions	Cpk>1.67	-	1/10/0	-	3/30/0	-	1/10/0	-
Test Group D - Die Fabrication Reliability Tests													

EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
BTI	D4	-	-	-	Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E - Electrical Verification Tests													
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2000 Volts	Device specific data [1]	Device specific data [1]	1/3/0	-	1/3/0	1/3/0
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	500 Volts	1/3/0	1/3/0	1/3/0	-	1/3/0	1/3/0
LU	E4	AEC Q100-004	1	6	Latch-Up	Per AEC Q100-004	-	Device specific data [1]	Device specific data [1]	1/6/0	-	1/6/0	1/6/0
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	Device specific data [1]	Device specific data [1]	3/90/0	3/90/0	1/30/0	1/30/0

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles
Ambient Operating Temperature by Automotive Grade Level:
Grade 0 (or E): -40C to +150C
Grade 1 (or Q): -40C to +125C
Grade 2 (or T): -40C to +105C
Grade 3 (or I) : -40C to +85C
E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):
Room/Hot/Cold : HTOL, ED
Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
Room : AC/uHAST
[1] Data collected for same silicon die in D package
Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Qualification Report

Approve Date 06-February-2024

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Name	Condition	Duration	Qual Device: ISO7721DWVR	Qual Device: ISO7720DWVR	QBS Reference: UCC23513QDWYQ1	QBS Reference: ISO6763QDWRQ1	QBS Reference: ISO7721QDWVRQ1	QBS Reference: ISO7720QDWVRQ1
HAST	A2	Biased HAST	130C/85%RH	96 Hours	-	-	-	3/231/0	-	-
UHAST	A3	Autoclave	121C/15psig	96 Hours	-	-	-	3/231/0	-	-
TC	A4	Temperature Cycle	-65C/150C	500 Cycles	-	-	-	3/231/0	-	-
HTSL	A6	High Temperature Storage Life	150C	1000 Hours	-	-	-	3/135/0	-	-
HTSL	A6	High Temperature Storage Life	175C	500 Hours	-	-	-	-	-	-
HTOL	B1	Life Test	125C	1000 Hours	-	-	3/231/0	-	-	-
ELFR	B2	Early Life Failure Rate	125C	48 Hours	-	-	3/2400/0	-	-	-

ESD	E2	ESD CDM	-	500 Volts	-	-	1/3/0	-	1/3/0	1/3/0
ESD	E2	ESD HBM	-	2000 Volts	-	-	1/3/0	-	1/3/0	1/3/0
LU	E4	Latch-Up	Per JESD78	-	-	-	1/6/0	-	1/6/0	1/6/0
CHAR	E5	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	-	-	3/90/0	-	1/30/0	1/30/0

QBS: Qual By Similarity
Qual Device ISO7721DWVR is qualified at MSL2 260C
Qual Device ISO7720DWVR is qualified at MSL2 260C
Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles
Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

For questions regarding this notice, e-mails can be sent to Change Management team or your local Field Sales Representative.